

74LV139

Dual 2-to-4 line decoder/demultiplexer

Rev. 04 — 13 December 2007

Product data sheet

1. General description

The 74LV139 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC139 and 74HCT139.

The 74LV139 is a dual 2-to-4 line decoder/demultiplexer. It has two independent decoders, each accepting two binary weighted inputs ($nA0$ and $nA1$) and providing four mutually exclusive outputs ($n\bar{Y}0$ to $n\bar{Y}3$) that are LOW when selected. Each decoder has an active LOW input ($n\bar{E}$). When $n\bar{E}$ is HIGH, every output is forced HIGH. The enable input can be used as the data input for a 1-to-4 demultiplexer application.

2. Features

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical output ground bounce < 0.8 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Demultiplexing capability
- Two independent 2-to-4 line decoders
- Multifunction capability
- Active LOW mutually exclusive outputs
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C

3. Ordering information

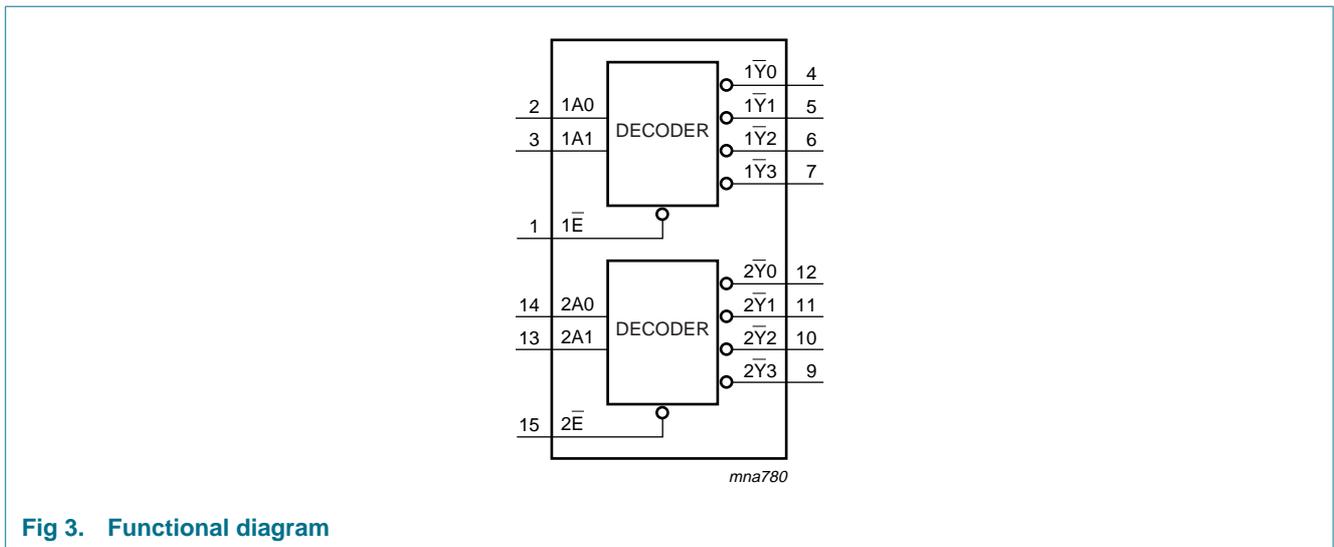
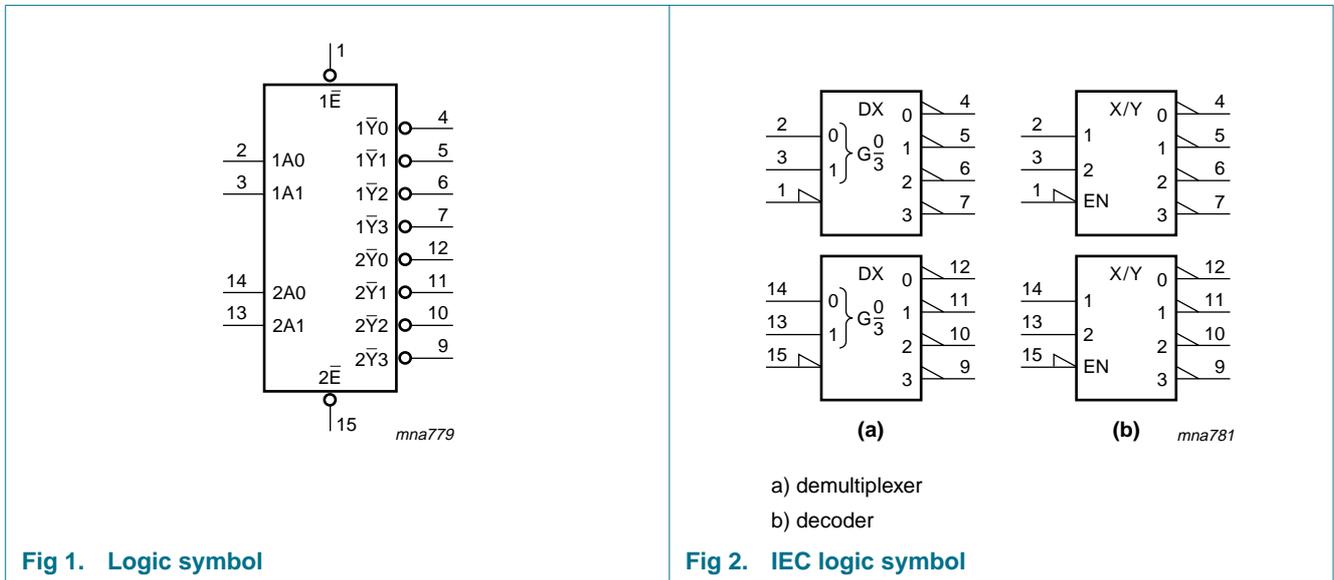
Table 1. Ordering information

| Type number | Package | | | |
|-------------|-----------------------|-------|--|----------|
| | Temperature range | Name | Description | Version |
| 74LV139N | -40 °C to $+125$ °C | DIP16 | plastic dual in-line package; 16 leads (300 mil) | SOT38-4 |
| 74LV139D | -40 °C to $+125$ °C | SO16 | plastic small outline package; 16 leads; body width 3.9 mm | SOT109-1 |

Table 1. Ordering information ...continued

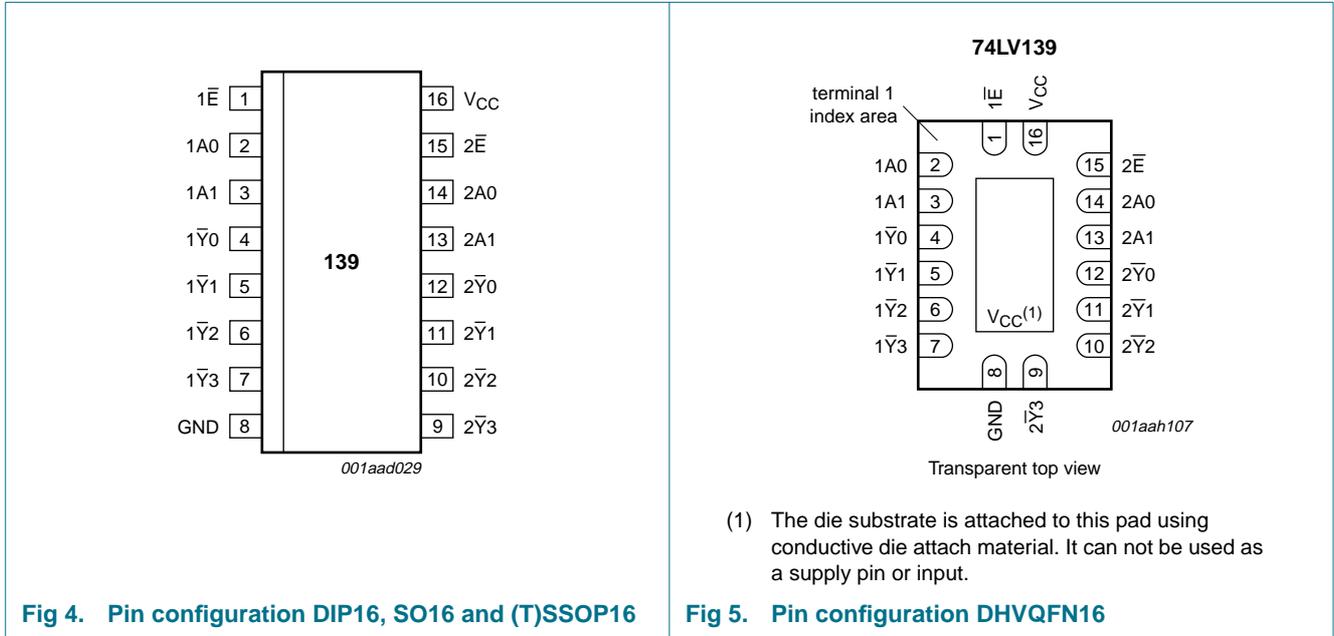
| Type number | Package | | | Version |
|-------------|-------------------|----------|--|----------|
| | Temperature range | Name | Description | |
| 74LV139DB | -40 °C to +125 °C | SSOP16 | plastic shrink small outline package; 16 leads; body width 5.3 mm | SOT338-1 |
| 74LV139PW | -40 °C to +125 °C | TSSOP16 | plastic thin shrink small outline package; 16 leads; body width 4.4 mm | SOT403-1 |
| 74LV139BQ | -40 °C to +125 °C | DHVQFN16 | plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm | SOT763-1 |

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

| Symbol | Pin | Description |
|-----------------|-----|---------------------------|
| 1E | 1 | enable input (active LOW) |
| 1A0 | 2 | address input |
| 1A1 | 3 | address input |
| 1Y0 | 4 | output |
| 1Y1 | 5 | output |
| 1Y2 | 6 | output |
| 1Y3 | 7 | output |
| GND | 8 | ground (0 V) |
| 2Y3 | 9 | output |
| 2Y2 | 10 | output |
| 2Y1 | 11 | output |
| 2Y0 | 12 | output |
| 2A0 | 14 | address input |
| 2A1 | 13 | address input |
| 2E | 15 | enable input (active LOW) |
| V _{CC} | 16 | supply voltage |

6. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care

| Input | | | Output | | | |
|-------|-----|-----|--------|-----|-----|-----|
| nE | nA0 | nA1 | nY0 | nY1 | nY2 | nY3 |
| H | X | X | H | H | H | H |
| L | L | L | L | H | H | H |
| L | H | L | H | L | H | H |
| L | L | H | H | H | L | H |
| L | H | H | H | H | H | L |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|--|-------|----------|------|
| V_{CC} | supply voltage | | -0.5 | +7.0 | V |
| I_{IK} | input clamping current | $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ | [1] - | ± 20 | mA |
| I_{OK} | output clamping current | $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ | [1] - | ± 50 | mA |
| I_O | output current | $V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$ | - | ± 25 | mA |
| I_{CC} | supply current | | - | 50 | mA |
| I_{GND} | ground current | | -50 | - | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | $T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$ | | | |
| | DIP16 package | | [2] - | 750 | mW |
| | SO16 package | | [3] - | 500 | mW |
| | (T)SSOP16 package | | [4] - | 500 | mW |
| | DHVQFN16 package | | [5] - | 500 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[5] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|-------------------------------------|---|---------|-----|----------|------|
| V_{CC} | supply voltage | | [1] 1.0 | 3.3 | 5.5 | V |
| V_I | input voltage | | 0 | - | V_{CC} | V |
| V_O | output voltage | | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 1.0\text{ V to }2.0\text{ V}$ | - | - | 500 | ns/V |
| | | $V_{CC} = 2.0\text{ V to }2.7\text{ V}$ | - | - | 200 | ns/V |
| | | $V_{CC} = 2.7\text{ V to }3.6\text{ V}$ | - | - | 100 | ns/V |
| | | $V_{CC} = 3.6\text{ V to }5.5\text{ V}$ | - | - | 50 | ns/V |

[1] The static characteristics are guaranteed from $V_{CC} = 1.2\text{ V}$ to $V_{CC} = 5.5\text{ V}$, but LV devices are guaranteed to function down to $V_{CC} = 1.0\text{ V}$ (with input levels GND or V_{CC}).

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|--|---------------------------|--|------------------|--------------------|-------------|-------------------|-------------|------|
| | | | Min | Typ ^[1] | Max | Min | Max | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 1.2\text{ V}$ | 0.9 | - | - | 0.9 | - | V |
| | | $V_{CC} = 2.0\text{ V}$ | 1.4 | - | - | 1.4 | - | V |
| | | $V_{CC} = 2.7\text{ V to }3.6\text{ V}$ | 2.0 | - | - | 2.0 | - | V |
| | | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | $0.7V_{CC}$ | - | - | $0.7V_{CC}$ | - | V |
| V_{IL} | LOW-level input voltage | $V_{CC} = 1.2\text{ V}$ | - | - | 0.3 | - | 0.3 | V |
| | | $V_{CC} = 2.0\text{ V}$ | - | - | 0.6 | - | 0.6 | V |
| | | $V_{CC} = 2.7\text{ V to }3.6\text{ V}$ | - | - | 0.8 | - | 0.8 | V |
| | | $V_{CC} = 4.5\text{ V to }5.5\text{ V}$ | - | - | $0.3V_{CC}$ | - | $0.3V_{CC}$ | V |
| V_{OH} | HIGH-level output voltage | $V_I = V_{IH}$ or V_{IL} | | | | | | |
| | | $I_O = -100\ \mu\text{A}; V_{CC} = 1.2\text{ V}$ | - | 1.2 | - | - | - | V |
| | | $I_O = -100\ \mu\text{A}; V_{CC} = 2.0\text{ V}$ | 1.8 | 2.0 | - | 1.8 | - | V |
| | | $I_O = -100\ \mu\text{A}; V_{CC} = 2.7\text{ V}$ | 2.5 | 2.7 | - | 2.5 | - | V |
| | | $I_O = -100\ \mu\text{A}; V_{CC} = 3.0\text{ V}$ | 2.8 | 3.0 | - | 2.8 | - | V |
| | | $I_O = -100\ \mu\text{A}; V_{CC} = 4.5\text{ V}$ | 4.3 | 4.5 | - | 4.3 | - | V |
| | | $I_O = -6\text{ mA}; V_{CC} = 3.0\text{ V}$ | 2.4 | 2.82 | - | 2.2 | - | V |
| $I_O = -12\text{ mA}; V_{CC} = 4.5\text{ V}$ | 3.6 | 4.2 | - | 3.5 | - | V | | |

Table 6. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|------------------|---------------------------|---|------------------|--------------------|------|-------------------|------|------|
| | | | Min | Typ ^[1] | Max | Min | Max | |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | |
| | | I _O = 100 μA; V _{CC} = 1.2 V | - | 0 | - | - | - | V |
| | | I _O = 100 μA; V _{CC} = 2.0 V | - | 0 | 0.2 | - | 0.2 | V |
| | | I _O = 100 μA; V _{CC} = 2.7 V | - | 0 | 0.2 | - | 0.2 | V |
| | | I _O = 100 μA; V _{CC} = 3.0 V | - | 0 | 0.2 | - | 0.2 | V |
| | | I _O = 100 μA; V _{CC} = 4.5 V | - | 0 | 0.2 | - | 0.2 | V |
| | | I _O = 6 mA; V _{CC} = 3.0 V | - | 0.25 | 0.40 | - | 0.50 | V |
| | | I _O = 12 mA; V _{CC} = 4.5 V | - | 0.35 | 0.55 | - | 0.65 | V |
| I _I | input leakage current | V _I = V _{CC} or GND; V _{CC} = 5.5 V | - | - | 1.0 | - | 1.0 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V | - | - | 20.0 | - | 160 | μA |
| ΔI _{CC} | additional supply current | per input; V _I = V _{CC} - 0.6 V; V _{CC} = 2.7 V to 3.6 V | - | - | 500 | - | 850 | μA |
| C _I | input capacitance | | - | 3.5 | - | - | - | pF |

[1] Typical values are measured at T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics
 GND = 0 V; For test circuit see [Figure 8](#).

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|-----------------|-------------------|---|------------------|--------------------|-----|-------------------|-----|------|
| | | | Min | Typ ^[1] | Max | Min | Max | |
| t _{pd} | propagation delay | nAn to n \bar{Y} n; see Figure 6 ^[2] | | | | | | |
| | | V _{CC} = 1.2 V | - | 70 | - | - | - | ns |
| | | V _{CC} = 2.0 V | - | 24 | 31 | - | 39 | ns |
| | | V _{CC} = 2.7 V | - | 18 | 23 | - | 29 | ns |
| | | V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF ^[3] | - | 11 | - | - | - | ns |
| | | V _{CC} = 3.0 V to 3.6 V ^[3] | - | 13 | 18 | - | 23 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | - | - | 15 | - | 19 | ns |
| | | n \bar{E} n to \bar{Y} n; see Figure 7 | | | | | | |
| | | V _{CC} = 1.2 V | - | 60 | - | - | - | ns |
| | | V _{CC} = 2.0 V | - | 20 | 27 | - | 34 | ns |
| | | V _{CC} = 2.7 V | - | 15 | 20 | - | 25 | ns |
| | | V _{CC} = 3.0 V to 3.6 V; C _L = 15 pF ^[3] | - | 10 | - | - | - | ns |
| | | V _{CC} = 3.0 V to 3.6 V ^[3] | - | 11 | 16 | - | 20 | ns |
| | | V _{CC} = 4.5 V to 5.5 V | - | - | 13 | - | 16 | ns |

Table 7. Dynamic characteristics ...continued
 GND = 0 V; For test circuit see [Figure 8](#).

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|-----------------|-------------------------------|---|------------------|--------------------|-----|-------------------|-----|------|
| | | | Min | Typ ^[1] | Max | Min | Max | |
| C _{PD} | power dissipation capacitance | C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC} | [4] - | 42 | - | - | - | pF |

- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V).
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz, f_o = output frequency in MHz
 C_L = output load capacitance in pF
 V_{CC} = supply voltage in V
 N = number of inputs switching
 Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms

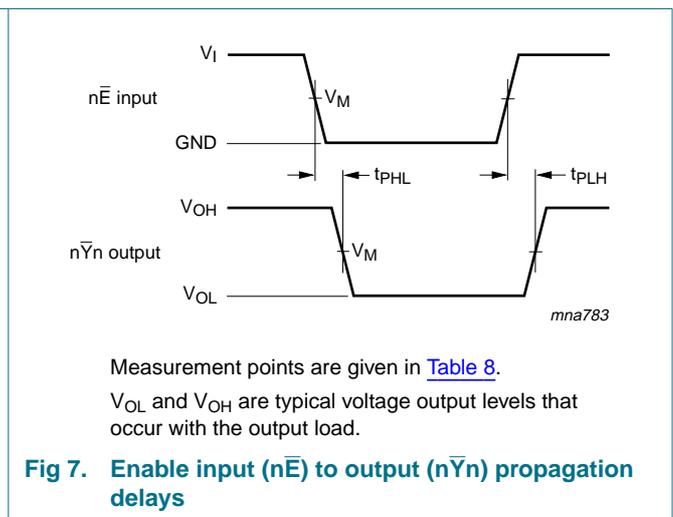
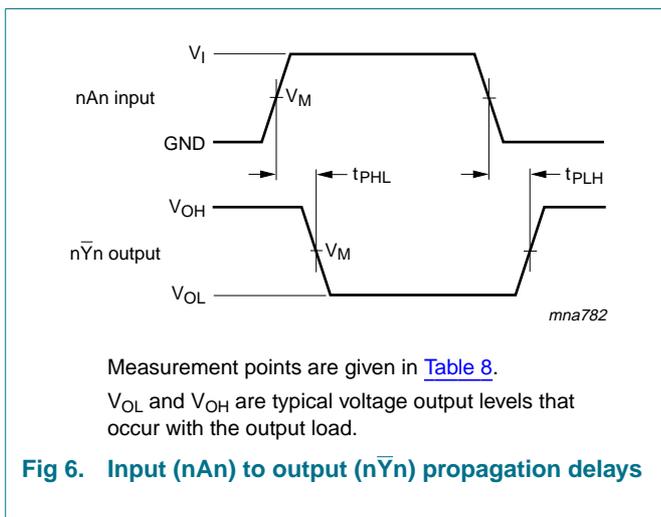
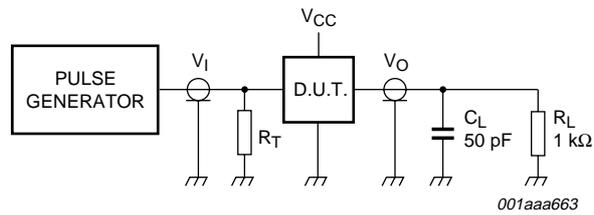


Table 8. Measurement points

| Supply voltage V _{CC} | Input V _M | Output V _M |
|--------------------------------|----------------------|-----------------------|
| < 2.7 V | 0.5V _{CC} | 0.5V _{CC} |
| 2.7 V to 3.6 V | 1.5 V | 1.5 V |
| ≥ 4.5 V | 0.5V _{CC} | 0.5V _{CC} |



Test data is given in [Table 9](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

Fig 8. Load circuit for switching times

Table 9. Test data

| Supply voltage | Input | t_r, t_f |
|----------------|----------|------------|
| V_{CC} | V_I | |
| < 2.7 V | V_{CC} | ≤ 2.5 ns |
| 2.7 V to 3.6 V | 2.7 V | ≤ 2.5 ns |
| ≥ 4.5 V | V_{CC} | ≤ 2.5 ns |

12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

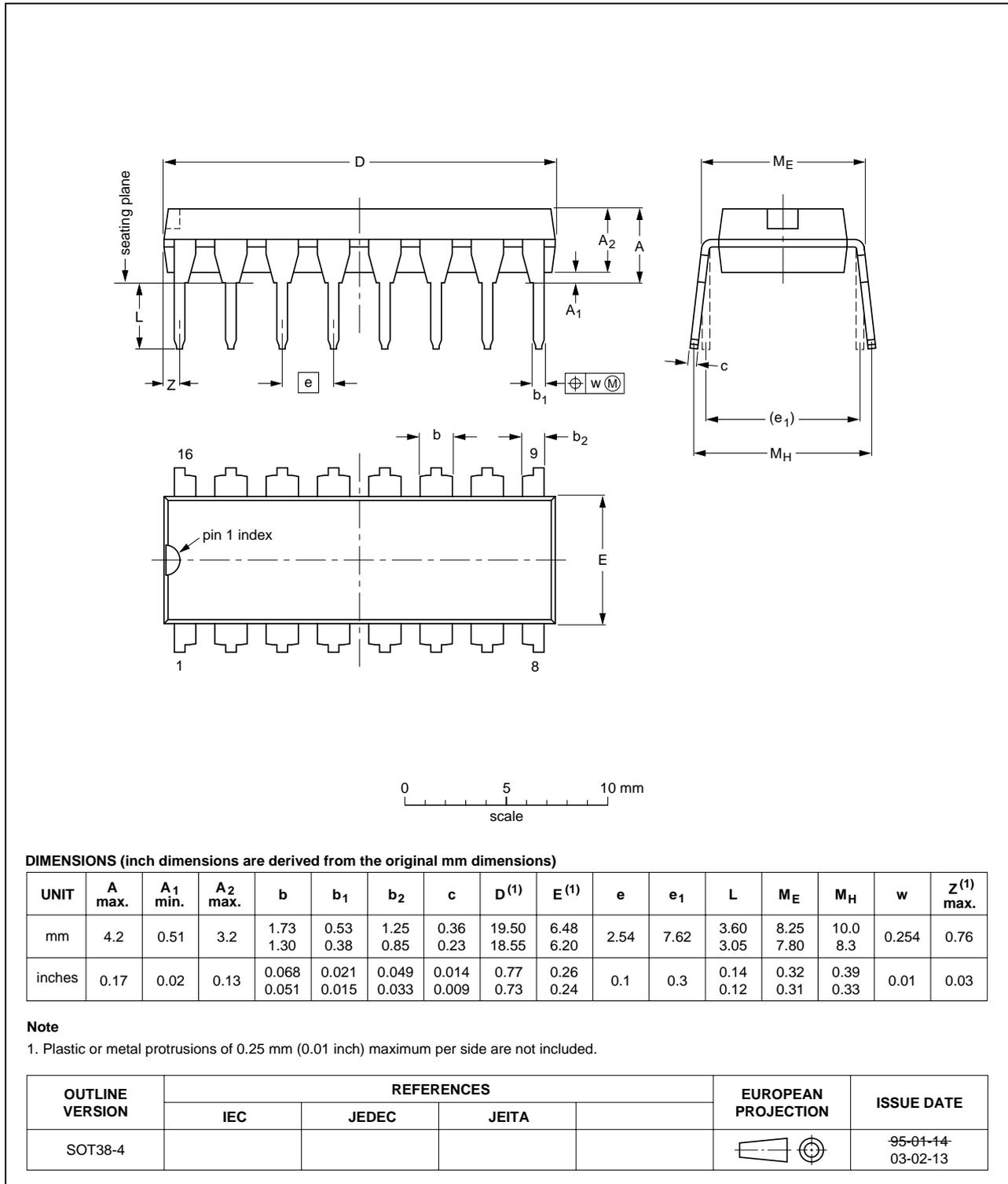


Fig 9. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

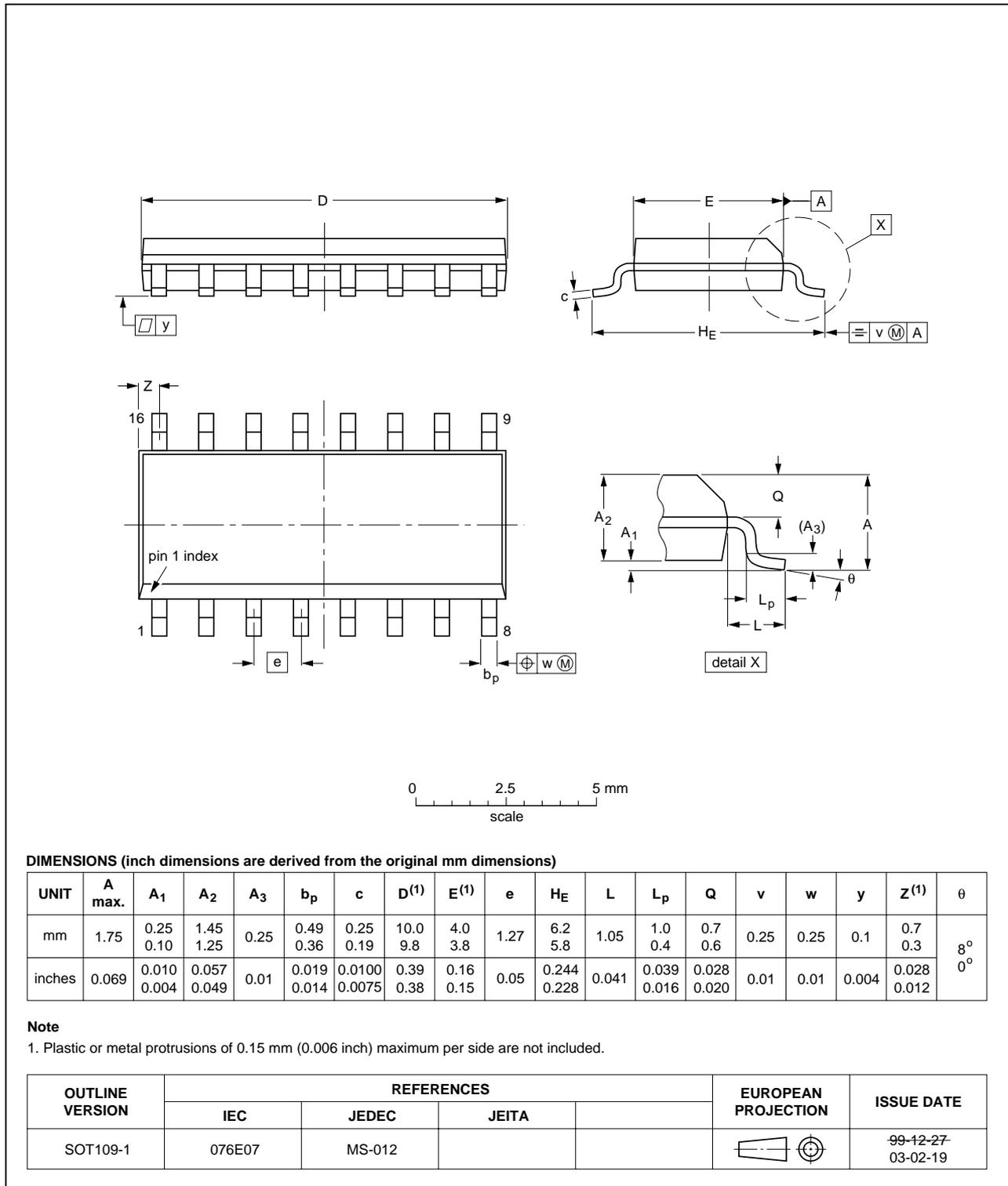


Fig 10. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

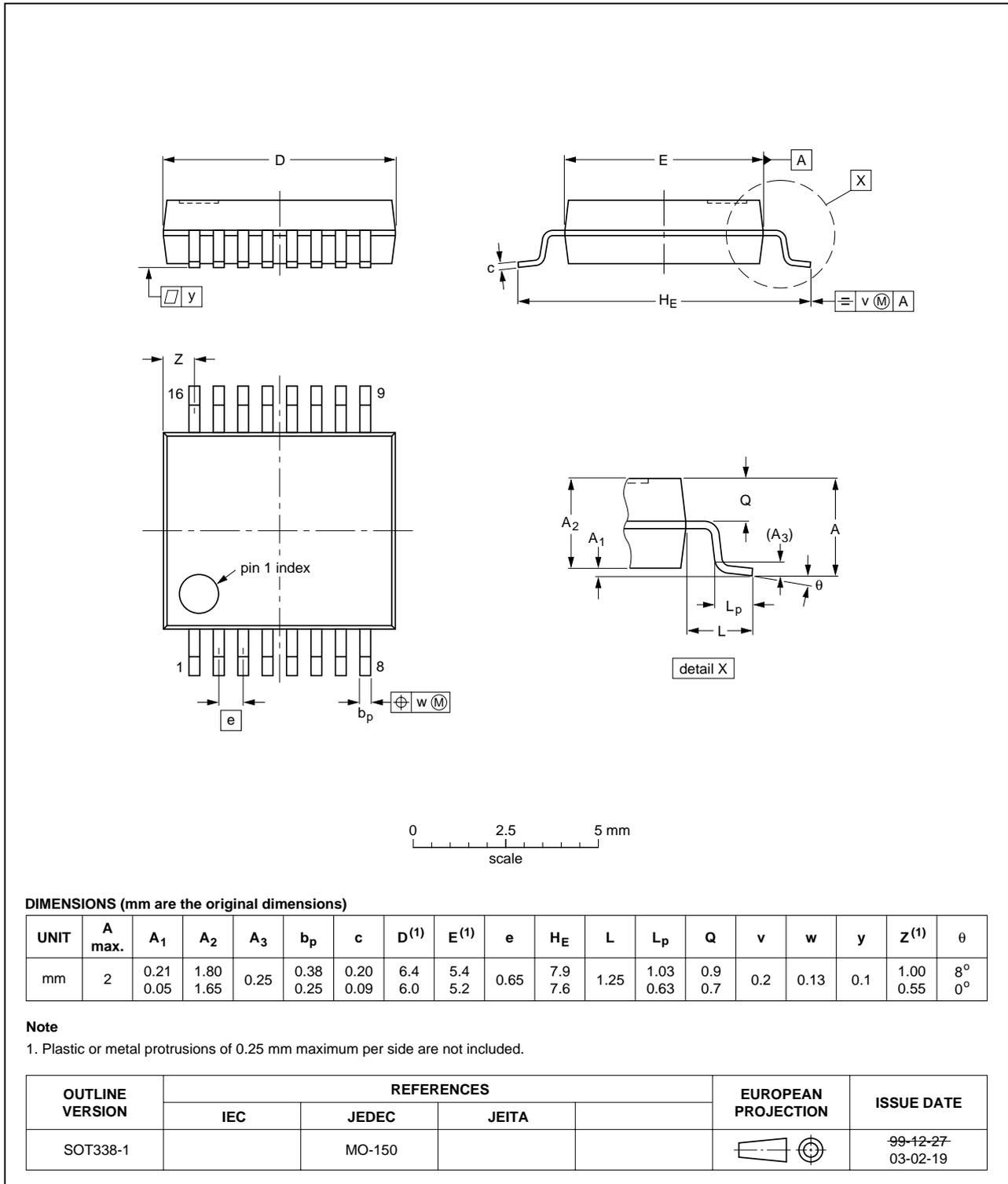


Fig 11. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

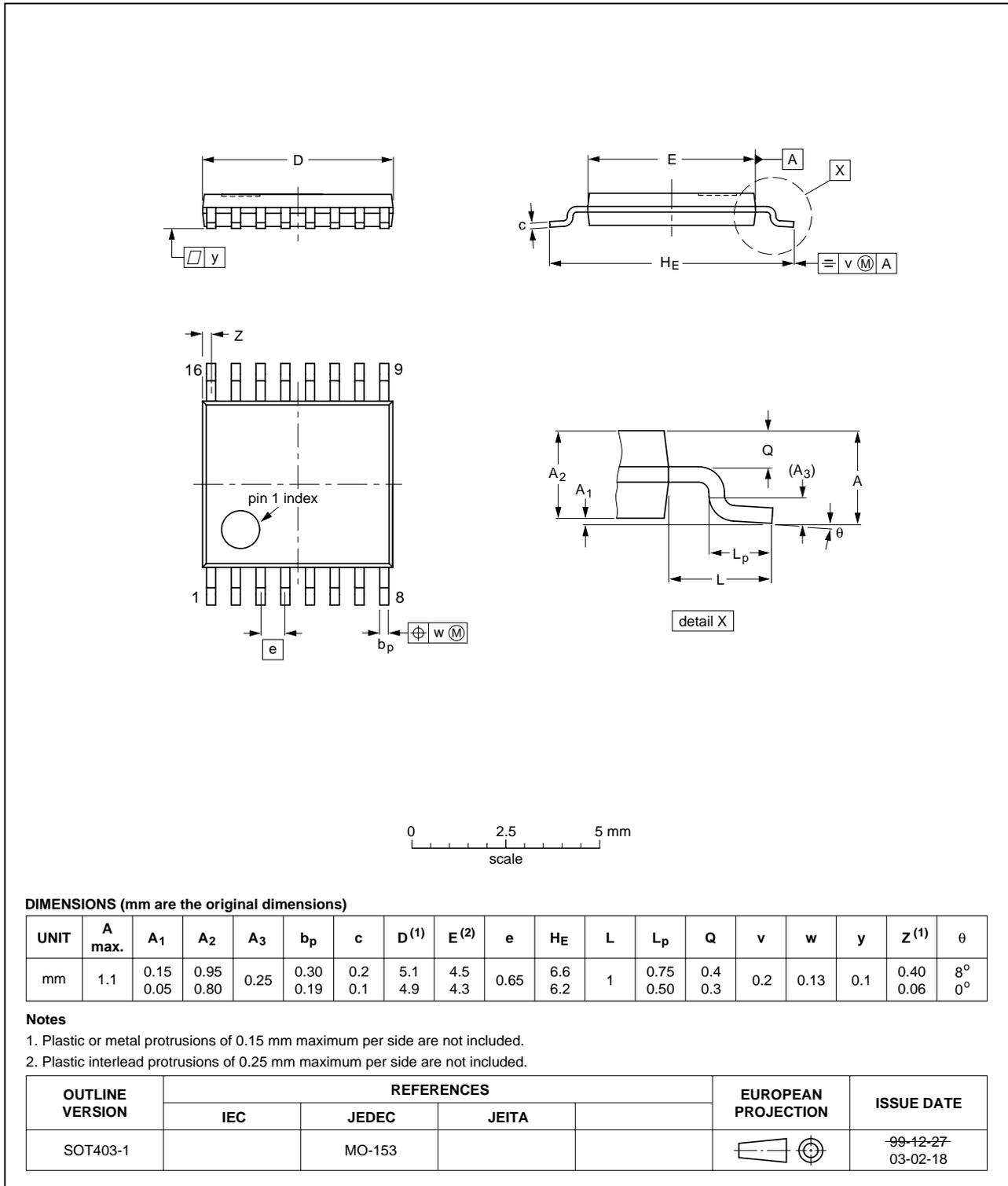


Fig 12. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

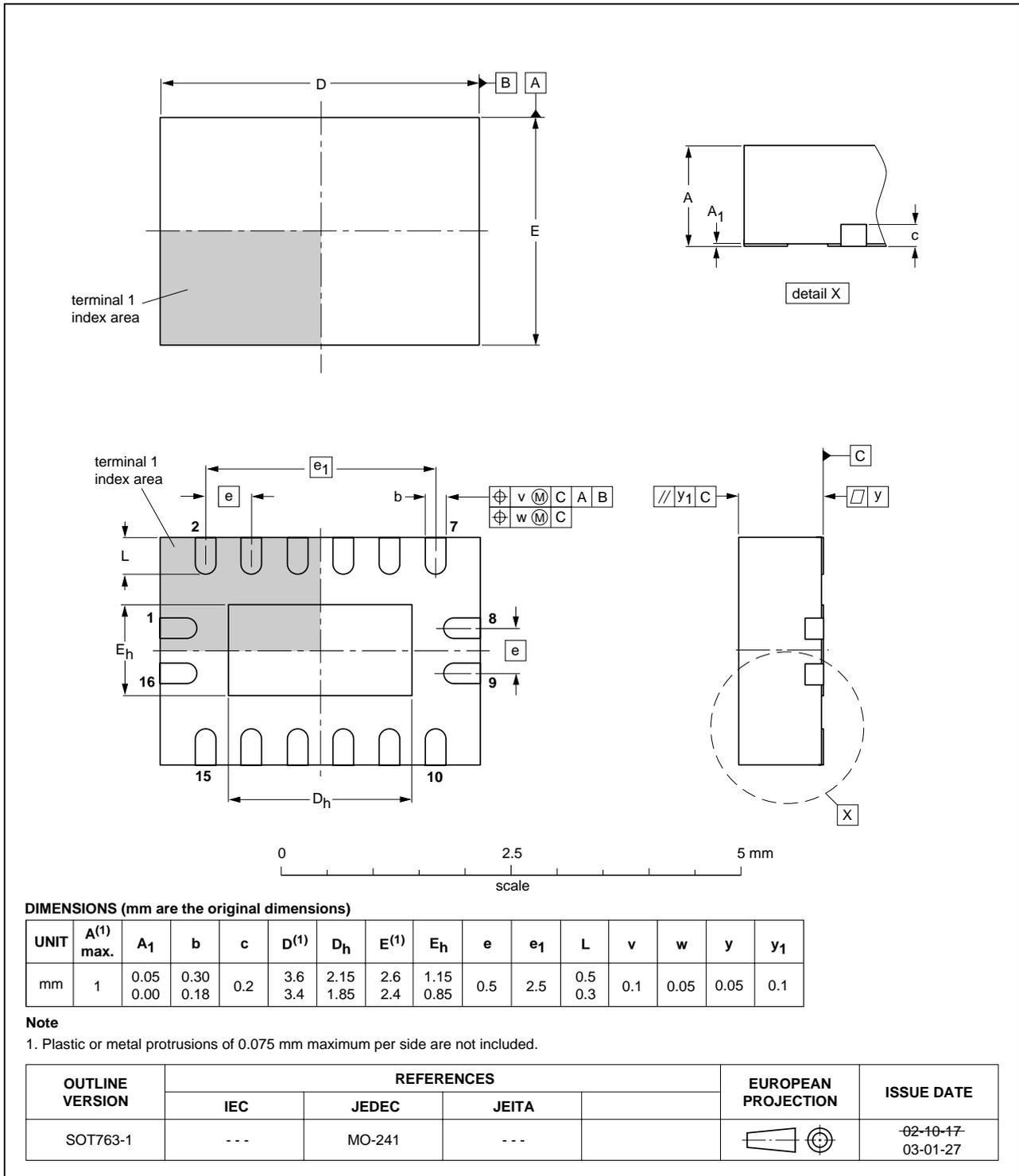


Fig 13. Package outline SOT763-1 (DHVQFN16)

13. Abbreviations

Table 10. Abbreviations

| Acronym | Description |
|---------|---|
| CMOS | Complementary Metal Oxide Semiconductor |
| DUT | Device Under Test |
| ESD | ElectroStatic Discharge |
| HBM | Human Body Model |
| MM | Machine Model |
| TTL | Transistor-Transistor Logic |

14. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--|-----------------------|---------------|------------|
| 74LV139_4 | 20071213 | Product data sheet | - | 74LV139_3 |
| Modifications: | <ul style="list-style-type: none"> • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3: DHVQFN16 package added. • Section 7: derating values added for DHVQFN16 package. • Section 12: outline drawing added for DHVQFN16 package. | | | |
| 74LV139_3 | 20030313 | Product specification | - | 74LV139_2 |
| 74LV139_2 | 19980428 | Product specification | - | 74LV139_1 |
| 74LV139_1 | 19970212 | Product specification | - | - |

15. Legal information

15.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 13 December 2007

Document identifier: 74LV139_4